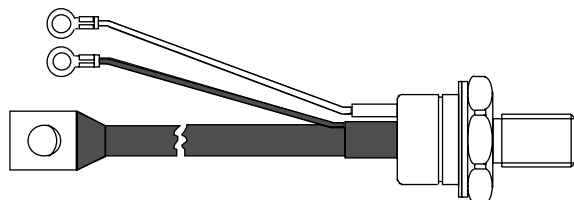


Phase Control Thyristors (Stud Version), 110 A



TO-209AC (TO-94)

FEATURES

- High current and high surge ratings
- Hermetic ceramic housing
- RoHS compliant
- Designed and qualified for industrial level



TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY

$I_{T(AV)}$	110 A
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MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		110	A
	T_C	90	°C
$I_{T(RMS)}$		172	A
I_{TSM}	50 Hz	2080	A
	60 Hz	2180	
I^2t	50 Hz	21.7	kA ² s
	60 Hz	19.8	
V_{DRM}/V_{RRM}		400 to 1200	V
t_q	Typical	110	μs
T_J		- 40 to 140	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
110/111RKI	40	400	500	20
	80	800	900	
	120	1200	1300	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			110	A
					90	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C case temperature			172	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	2080	A
		t = 8.3 ms			2180	
		t = 10 ms	100 % V _{RRM} reapplied		1750	
		t = 8.3 ms			1830	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		21.7	kA ² s
		t = 8.3 ms			19.8	
		t = 10 ms	100 % V _{RRM} reapplied		15.3	
		t = 8.3 ms			14.0	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			217	kA ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.82	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.02	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			2.16	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.70	
Maximum on-state voltage	V _{TM}	I _{pk} = 350 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.57	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 6 V resistive load			200	mA
Typical latching current	I _L				400	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1 \text{ μs}$ $T_J = T_J \text{ maximum}$, anode voltage $\leq 80 \% V_{DRM}$	300	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1 \text{ A/μs}$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 \text{ °C}$	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 50 \text{ A}$, $T_J = T_J \text{ maximum}$, $di/dt = -5 \text{ A/μs}$, $V_R = 50 \text{ V}$, $dV/dt = 20 \text{ V/μs}$; gate 0 V 25 Ω	110	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ maximum}$ linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J \text{ maximum}$, rated V_{DRM}/V_{RRM} applied	20	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		12		W
Maximum average gate power	P _{G(AV)}	T _J = T _J maximum, f = 50 Hz, d% = 50		3.0		
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+V _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		20		V
Maximum peak negative gate voltage	-V _{GM}			10		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		T _J = 25 °C		80	120	
		T _J = 140 °C		40	-	
DC gate voltage required to trigger	V _{GT}	T _J = - 40 °C		2.5	-	V
		T _J = 25 °C		1.6	2	
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	6.0		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 140	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.27	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.1	
Mounting torque, ± 10 %		Non-lubricated threads	15.5 (137)	N · m (lbf · in)
		Lubricated threads	14 (120)	
Approximate weight			130	g
Case style		See dimensions - link at the end of datasheet	TO-209AC (TO-94)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.043	0.031	$T_J = T_J$ maximum	K/W
120°	0.052	0.053		
90°	0.066	0.071		
60°	0.096	0.101		
30°	0.167	0.169		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

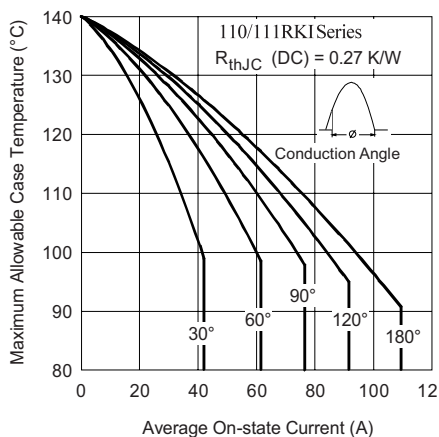


Fig. 1 - Current Ratings Characteristics

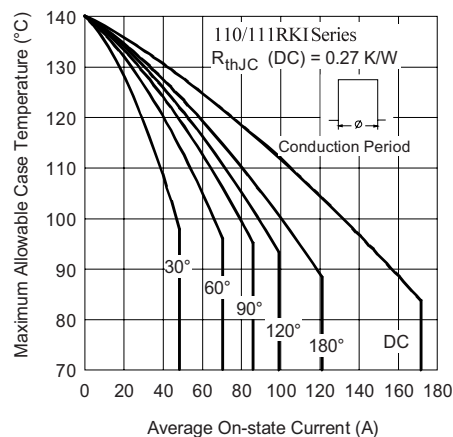


Fig. 2 - Current Ratings Characteristics

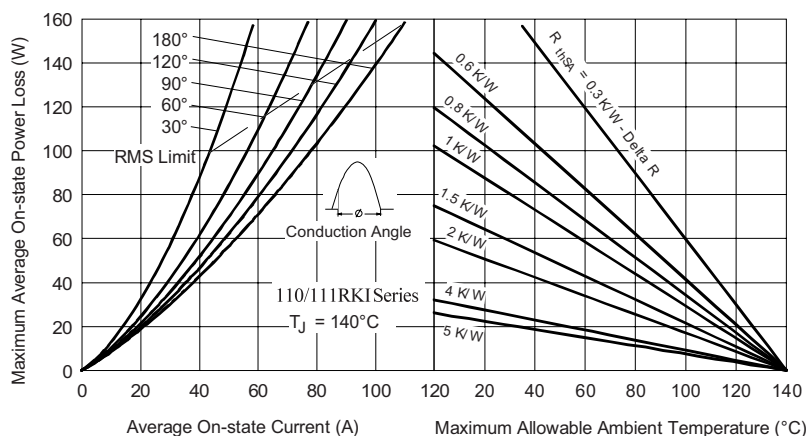


Fig. 3 - On-State Power Loss Characteristics

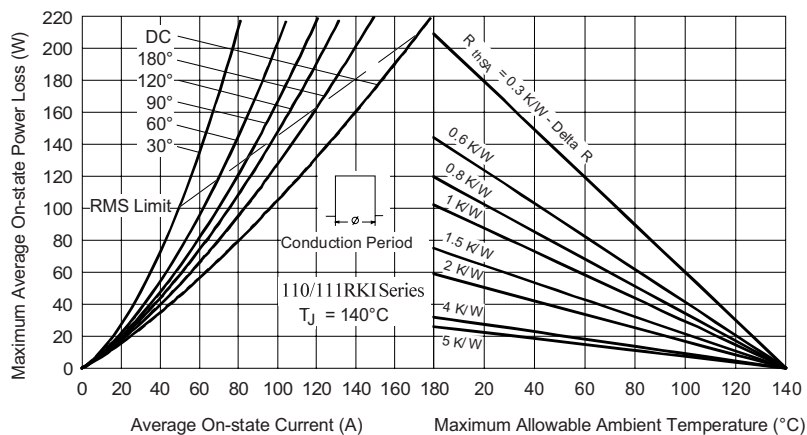


Fig. 4 - On-State Power Loss Characteristics

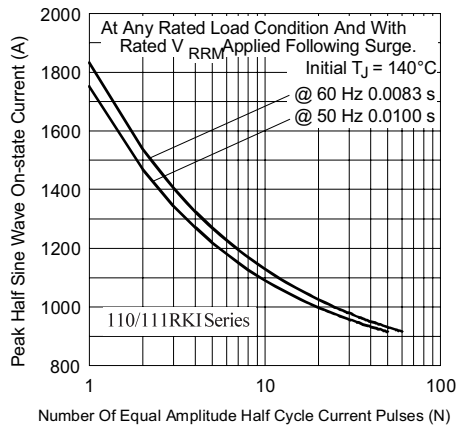


Fig. 5 - Maximum Non-Repetitive Surge Current

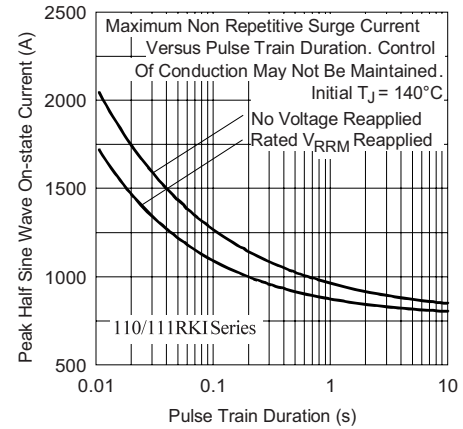


Fig. 6 - Maximum Non-Repetitive Surge Current

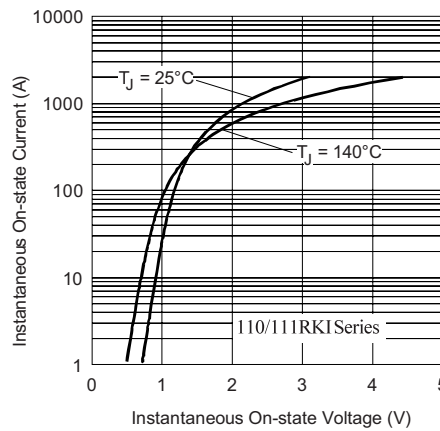


Fig. 7 - On-State Voltage Drop Characteristics

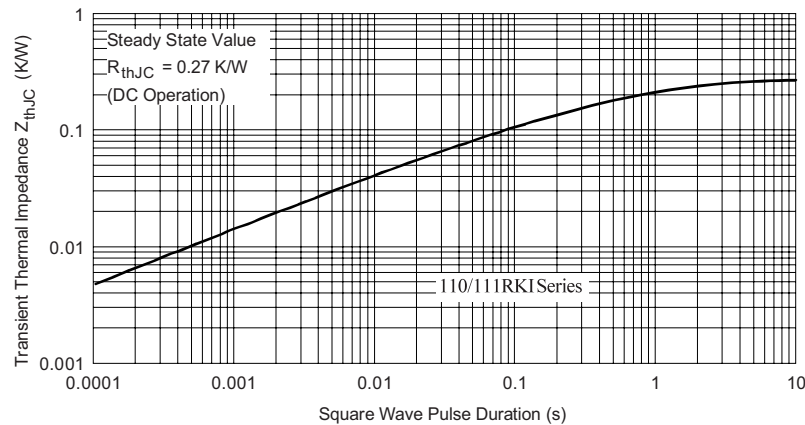


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

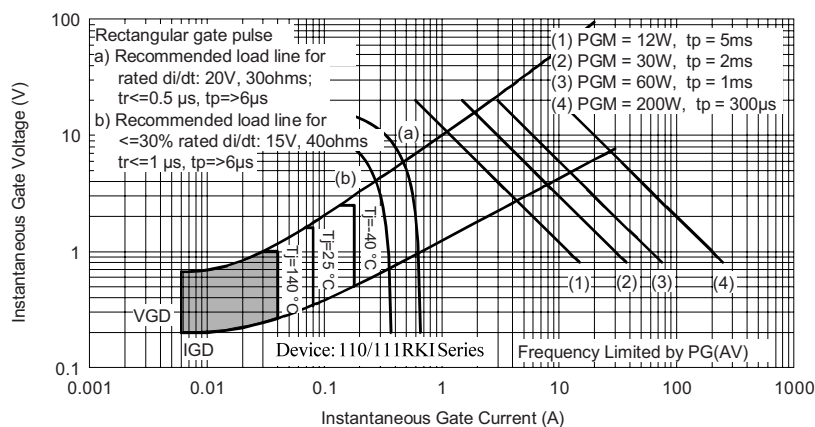


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	11	1	RKI	120
	①	②	③	④
	1	0	Thyristor	Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

1 - $I_{T(AV)}$ rated average output current (rounded/10)
2 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
 1 = Fast-on terminals (gate and auxiliary cathode leads)
3 - Thyristor
4 - Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

LINKS TO RELATED DOCUMENTS

Dimensions	http://www.vishay.com/doc?95003
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